



FQI2P25TU Information



For Reference Only

Part Number FQI2P25TU

 Manufacturer
 Fairchild/ON Semiconductor

 Category
 Discrete Semiconductor Products

 Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 250V 2.3A I2PAK

Package TO-262-3 Long Leads, I2Pak, TO-262AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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FQI2P25TU Specifications

Manufacturer Part Number FQI2P25TU Manufacturer Fairchild/ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-262-3 Long Leads, I2Pak, TO-262AA Series QFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 2.3A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 8.5nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 250pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.13W (Ta), 52W (Tc) Rds On (Max) @ Id, Vgs 4 Ohm @ 1.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 12PAK Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-262-3 Long Leads, 12Pak, TO-262AASeriesQFET?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C2.3A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs8.5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds250pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.13W (Ta), 52W (Tc)Rds On (Max) @ Id, Vgs4 Ohm @ 1.15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package12PAKPackage / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Manufacturer Part Number	FQI2P25TU
Package TO-262-3 Long Leads, 12Pak, TO-262AA Series QFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 2.3A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 8.5nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 250pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.13W (Ta), 52W (Tc) Rds On (Max) @ Id, Vgs 4 Ohm @ 1.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 12PAK Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA	Manufacturer	Fairchild/ON Semiconductor
Package TC-262-3 Long Leads, I2Pak, TC-262AA Series QFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 2.3A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 8.5nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 250pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.13W (Ta), 52W (Tc) Rds On (Max) @ Id, Vgs 4 Ohm @ 1.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 12PAK Package / Case 150°C (Assert Constitution of the properties of the package (To-262-3 Long Leads, 12Pak, TO-262AA)	Category	Discrete Semiconductor Products
Series QFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 2.3A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 8.5nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 250pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.13W (Ta), 52W (Tc) Rds On (Max) @ Id, Vgs 4 Ohm @ 1.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 12PAK Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA		Transistors - FETs, MOSFETs - Single
FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 2.3A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 8.5nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 250pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.13W (Ta), 52W (Tc) Rds On (Max) @ Id, Vgs 4 Ohm @ 1.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 12PAK Package / Case Toothon 12 Too 12 To	Package	TO-262-3 Long Leads, I2Pak, TO-262AA
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Sv @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature - Supplier Device Package Package / Case MOSFET (Metal Oxide) 250V 250V 250V 2.3A (Tc) 10V 5V @ 250μA 8.5nC @ 10V 250pF @ 25V 250pF @ 25V 4 Ohm 250V 250PF @ 25V 4 Ohm @ 1.15A, 10V 1.15A	Series	QFET?
Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C2.3A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs8.5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds250pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.13W (Ta), 52W (Tc)Rds On (Max) @ Id, Vgs4 Ohm @ 1.15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package12PAKPackage / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 8.5nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 250pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4 Ohm @ 1.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs8.5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds250pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.13W (Ta), 52W (Tc)Rds On (Max) @ Id, Vgs4 Ohm @ 1.15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package12PAKPackage / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Drain to Source Voltage (Vdss)	250V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) As On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case Sun 250μA 8.5nC @ 10V 250μF @ 25V 250μF @ 25ν 250	Current - Continuous Drain (Id) @ 25°C	2.3A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4 Ohm @ 1.15A, 10V Operating Temperature Jordan Temperature Mounting Type Through Hole Supplier Device Package TO-262-3 Long Leads, I2Pak, TO-262AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 250pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4 Ohm @ 1.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.13W (Ta), 52W (Tc) Rds On (Max) @ Id, Vgs 4 Ohm @ 1.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Gate Charge (Qg) (Max) @ Vgs	8.5nC @ 10V
FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4 Ohm @ 1.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Input Capacitance (Ciss) (Max) @ Vds	250pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4 Ohm @ 1.15A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs4 Ohm @ 1.15A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI2PAKPackage / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Power Dissipation (Max)	3.13W (Ta), 52W (Tc)
Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Rds On (Max) @ Id, Vgs	4 Ohm @ 1.15A, 10V
Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Mounting Type	Through Hole
	Supplier Device Package	I2PAK
Report errors?	Package / Case	TO-262-3 Long Leads, I2Pak, TO-262AA
		Report errors?

FQI2P25TU Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FQI2P25TU Payment Methods



















FQI2P25TU Shipping Methods













If you have any question about FQI2P25TU, please do not hesitate to contact us!

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